

Pin Configuration

KS/K Package
(SC-70-5/SOT-23-5)

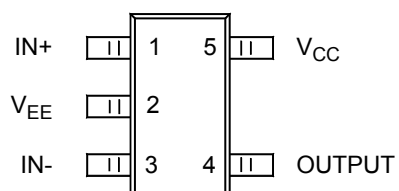


Figure 2. Pin Configuration of AZV321 (Top View)

Functional Block Diagram

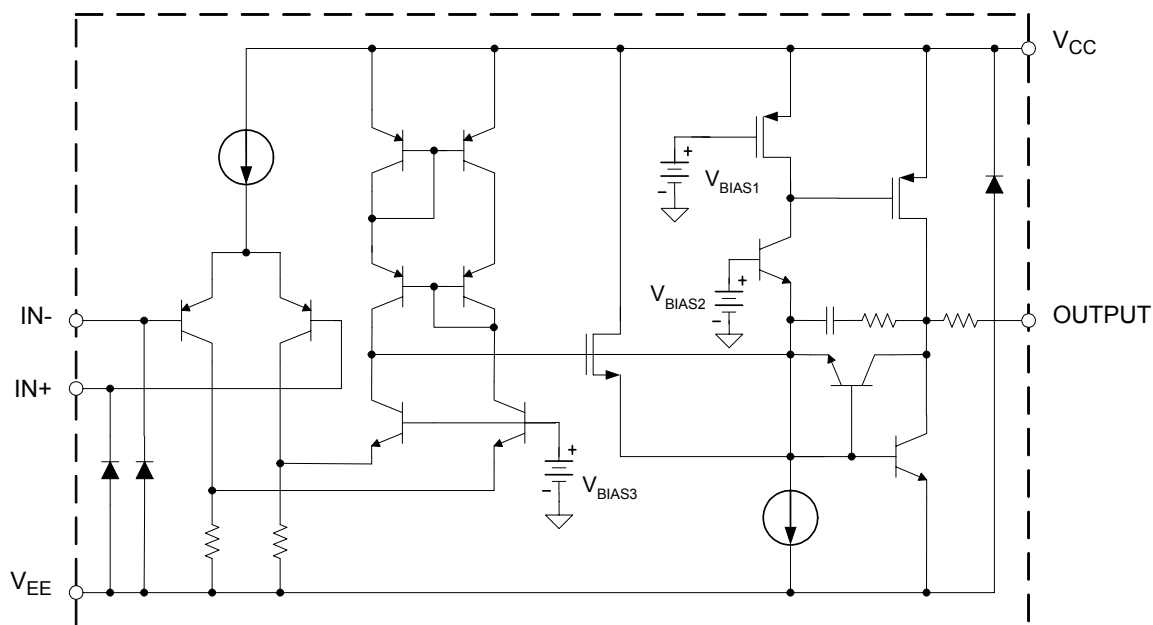
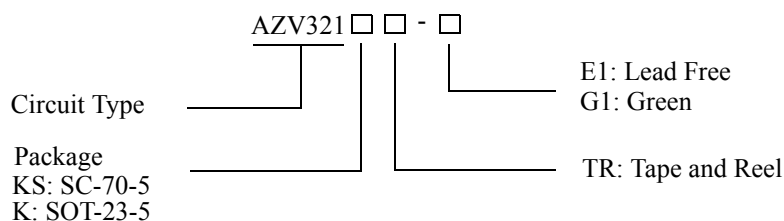


Figure 3. Functional Block Diagram of AZV321

**SINGLE LOW VOLTAGE RAIL-TO-RAIL OUTPUT OPERATIONAL AMPLIFIER****AZV321****Ordering Information**

Package	Temperature Range	Part Number		Marking ID		Packing Type
		Lead Free	Green	Lead Free	Green	
SC-70-5	-40 to 85°C	AZV321KSTR-E1	AZV321KSTR-G1	21	B1	Tape & Reel
SOT-23-5	-40 to 85°C	AZV321KTR-E1	AZV321KTR-G1	E6D	G6D	Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit
Power Supply Voltage	V_{CC}	6	V
Operation Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-65 to 150	°C
Lead Temperature (Soldering, 10 Seconds)	T_{LEAD}	260	°C
ESD (Machine Model)		200	V
ESD (Human Body Model)		2000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	2.7	5.5	V
Ambient Operating Temperature Range	T_A	-40	85	°C

**SINGLE LOW VOLTAGE RAIL-TO-RAIL OUTPUT OPERATIONAL AMPLIFIER****AZV321****2.7V Electrical Characteristics**

All limits are guaranteed for $T_A=25^\circ\text{C}$, $V_{CC}=2.7\text{V}$, $V_{EE}=0\text{V}$, $V_{CM}=1.0\text{V}$, $V_O=V_{CC}/2$ and $R_L>1\text{M}\Omega$, limits in **bold types** are guaranteed for $T_A=-40$ to 85°C , unless otherwise specified. (Note 2)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}			1.7	7	mV
					9	
Input Bias Current	I_B			11	250	nA
					500	
Input Offset Current	I_{IO}			5	50	nA
					150	
Input Common Mode Voltage Range	V_{CM}	for $\text{CMRR} \geq 50\text{dB}$	-0.1		1.9	V
Supply Current	I_{CC}	$V_O=V_{CC}/2$, $A_{VCL}=1$, no load		80	170	μA
					270	
Common Mode Rejection Ratio	CMRR	$0 \leq V_{CM} \leq 1.7\text{V}$	50	65		dB
Power Supply Rejection Ratio	PSRR	$2.7\text{V} \leq V_{CC} \leq 5\text{V}$, $V_O=1\text{V}$,	50	60		dB
Output Short Circuit Current	I_{SOURCE}	$V_O=0\text{V}$	5	20		mA
	I_{SINK}	$V_O=2.7\text{V}$	10	30		mA
Output Voltage Swing	V_{OH}	$R_L=10\text{k}\Omega$ to 1.35V	2.60	2.69		V
	V_{OL}			60	180	mV
Gain Bandwidth Product	GBWP	$C_L=200\text{pF}$		1		MHz
Phase Margin	ϕ_M			60		Deg
Gain Margin	G_M			10		dB

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.



SINGLE LOW VOLTAGE RAIL-TO-RAIL OUTPUT OPERATIONAL AMPLIFIER AZV321

5V Electrical Characteristics

All limits are guaranteed for $T_A=25^{\circ}\text{C}$, $V_{CC}=5\text{V}$, $V_{EE}=0\text{V}$, $V_{CM}=2.0\text{V}$, $V_O=V_{CC}/2$ and $R_L>1\text{M}\Omega$, limits in **bold types** are guaranteed for $T_A=-40$ to 85°C , unless otherwise specified. (Note 2)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}			1.7	7	mV
					9	
Input Bias Current	I_B			11	250	nA
					500	
Input Offset Current	I_{IO}			5	50	nA
					150	
Input Common Mode Voltage Range	V_{CM}	for $\text{CMRR} \geq 50\text{dB}$	-0.1		4.2	V
Supply Current	I_{CC}	$V_O=V_{CC}/2$, $A_{VCL}=1$, no load		130	250	μA
					350	
Large Signal Voltage Gain	G_V	$R_L=2\text{k}\Omega$	84	100		dB
			80			
Common Mode Rejection Ratio	CMRR	$0 \leq V_{CM} \leq 4\text{V}$	50	65		dB
Power Supply Rejection Ratio	PSRR	$2.7\text{V} \leq V_{CC} \leq 5\text{V}$, $V_O=1\text{V}$, $V_{CM}=1\text{V}$	50	60		dB
Output Short Circuit Current	I_{SOURCE}	$V_O=0\text{V}$	5	60		mA
	I_{SINK}	$V_O=5\text{V}$	10	160		mA
Output Voltage Swing	V_{OH}	$R_L=2\text{k}\Omega$ to 2.5V	4.7	4.96		V
			4.6			
		$R_L=10\text{k}\Omega$ to 2.5V	4.9	4.99		
			4.8			
	V_{OL}	$R_L=2\text{k}\Omega$ to 2.5V		120	300	mV
					400	
		$R_L=10\text{k}\Omega$ to 2.5V		65	180	
					280	
Slew Rate	SR			1		V/ μS
Gain Bandwidth Product	GBWP	$C_L=200\text{pF}$		1		MHz
Phase Margin	ϕ_M			60		Deg
Gain Margin	G_M			10		dB

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.



Typical Performance Characteristics

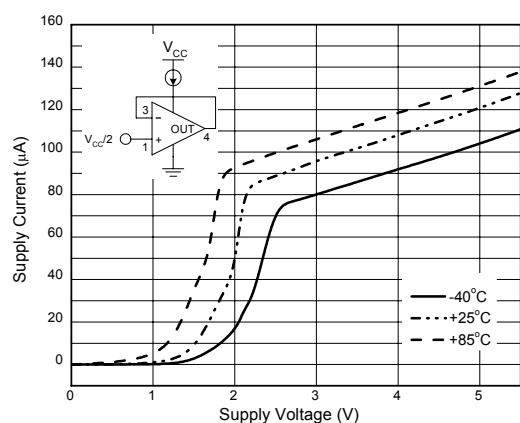


Figure 4. Supply Current vs. Supply Voltage

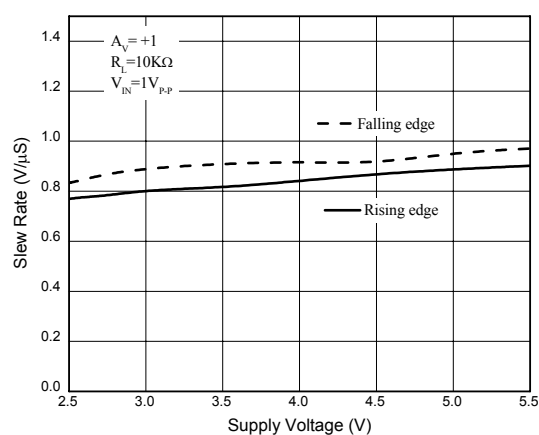


Figure 5. Slew Rate vs. Supply Voltage

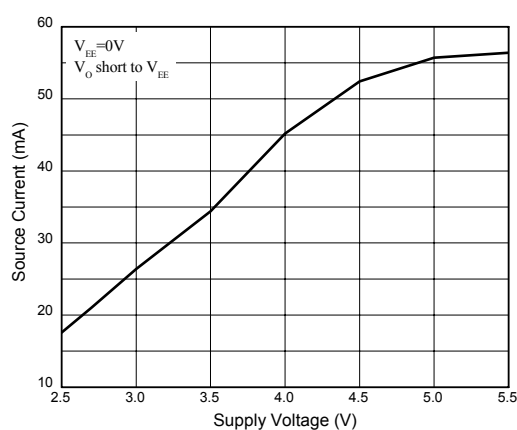


Figure 6. Output Source Current vs. Supply Voltage

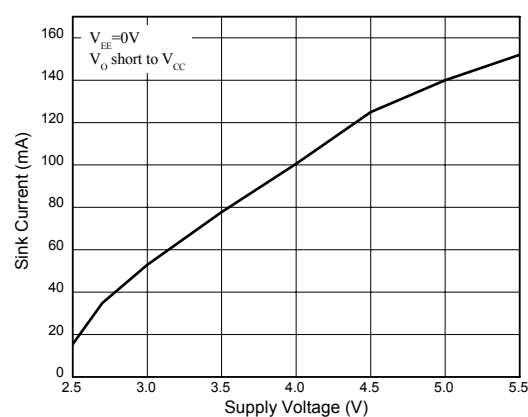


Figure 7. Output Sink Current vs. Supply Voltage



Typical Performance Characteristics (Continued)

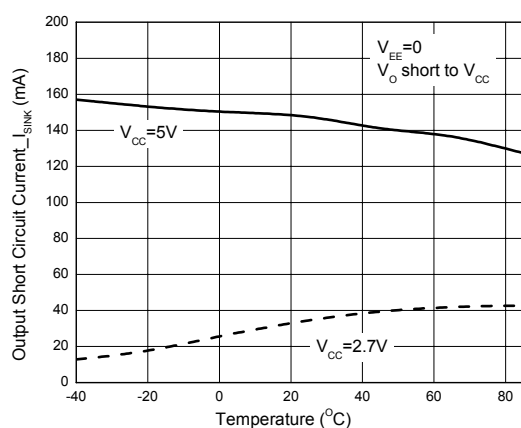
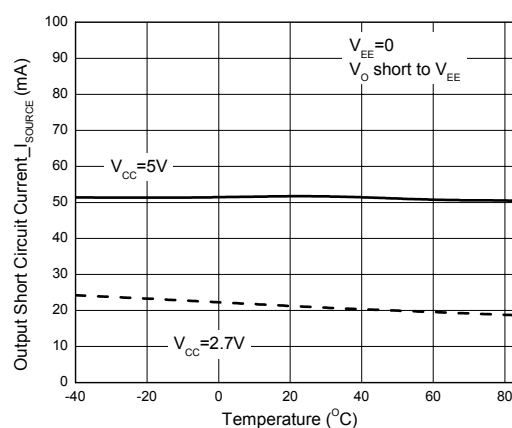
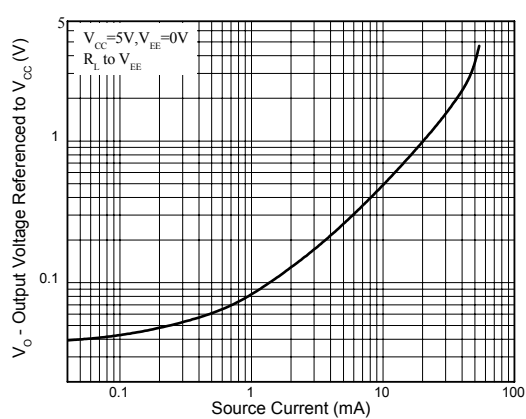
Figure 8. Short Circuit Current I_{SINK} vs. TemperatureFigure 9. Short Circuit Current I_{SOURCE} vs. Temperature

Figure 10. Output Voltage vs. Source Current

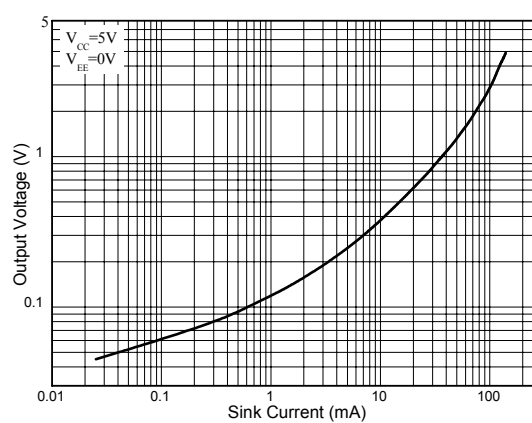


Figure 11. Output Voltage vs. Sink Current



Typical Performance Characteristics (Continued)

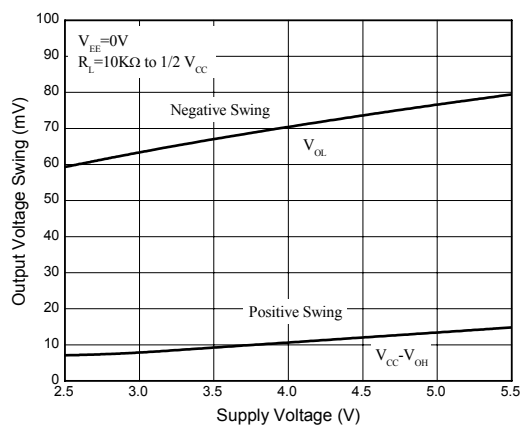


Figure 12. Output Voltage Swing vs. Supply Voltage

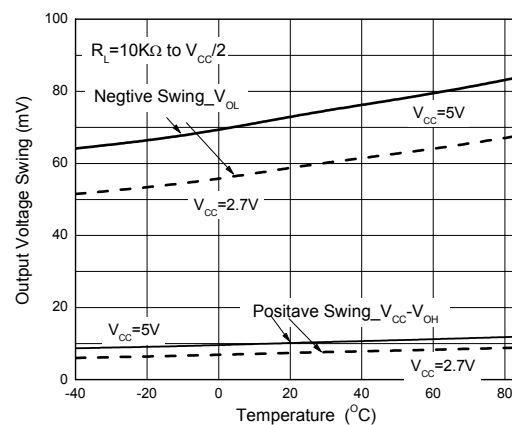
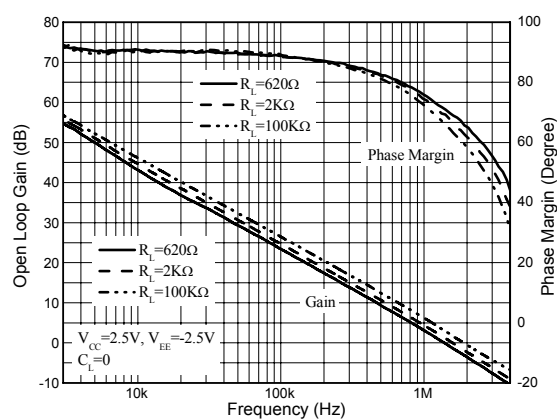


Figure 13. Output Voltage Swing vs. Temperature

Figure 14. Gain and Phase
vs. Frequency and Resistive Load



Typical Performance Characteristics (Continued)

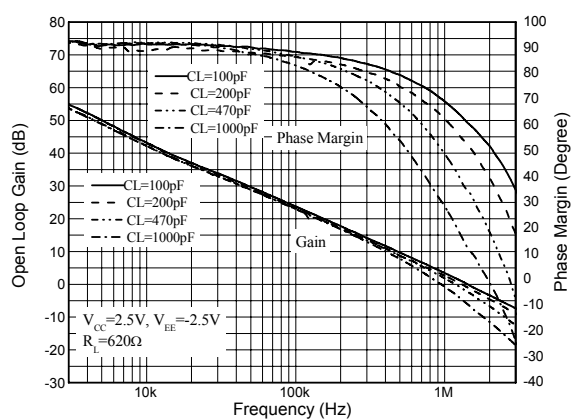


Figure 15. Gain and Phase vs. Frequency and Capacitive Load

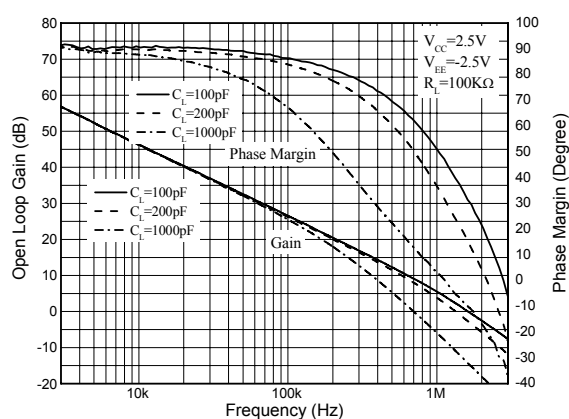


Figure 16. Gain and Phase vs. Frequency and Capacitive Load

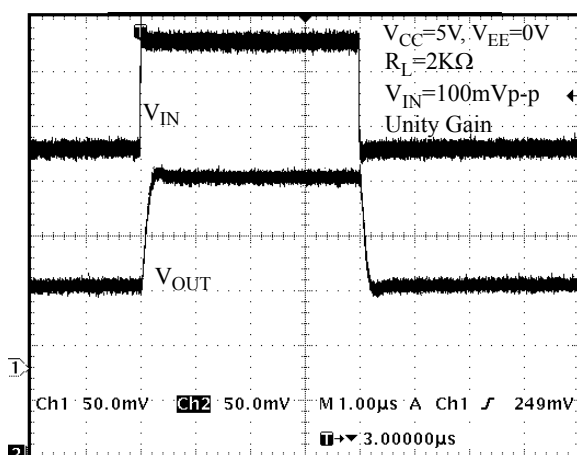


Figure 17. Non-Inverting Input Small Signal Pulse Response

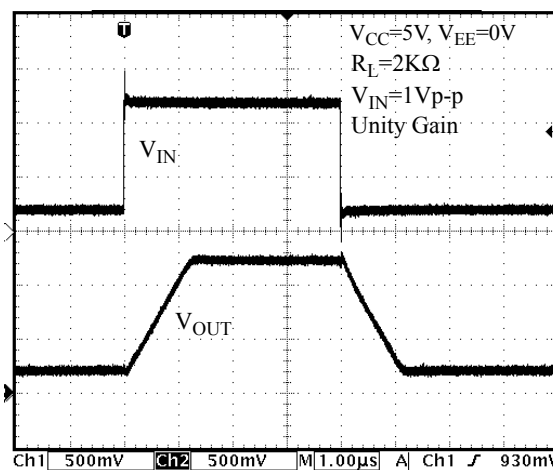


Figure 18. Non-Inverting Input Large Signal Pulse Response



Typical Performance Characteristics (Continued)

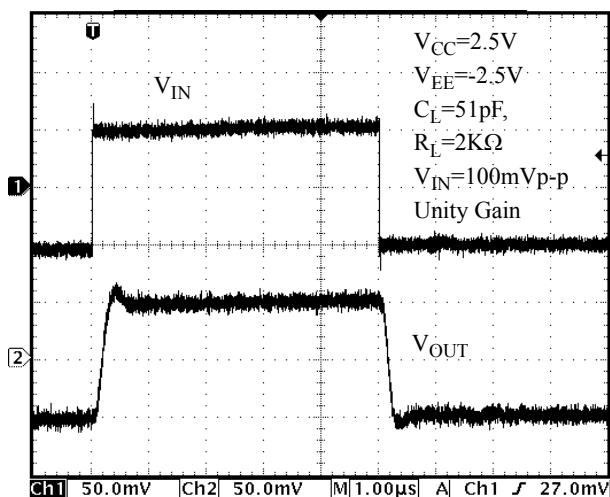


Figure 19. Output with Excessive Capacitive Load

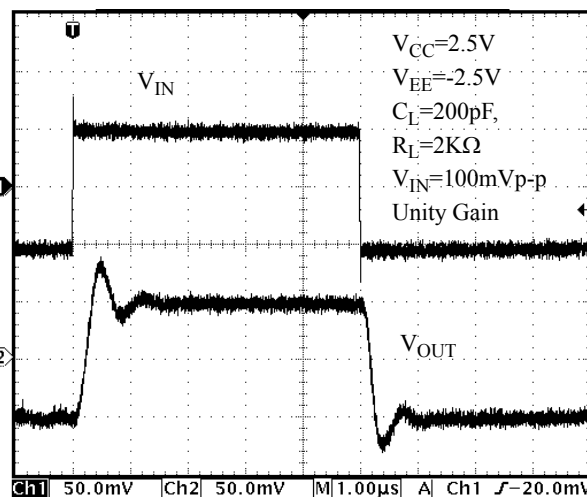


Figure 20. Output with Excessive Capacitive Load

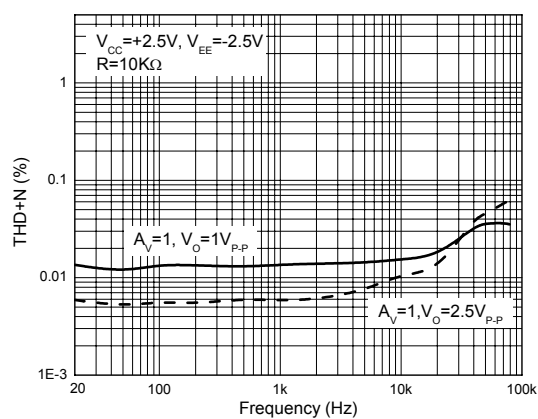


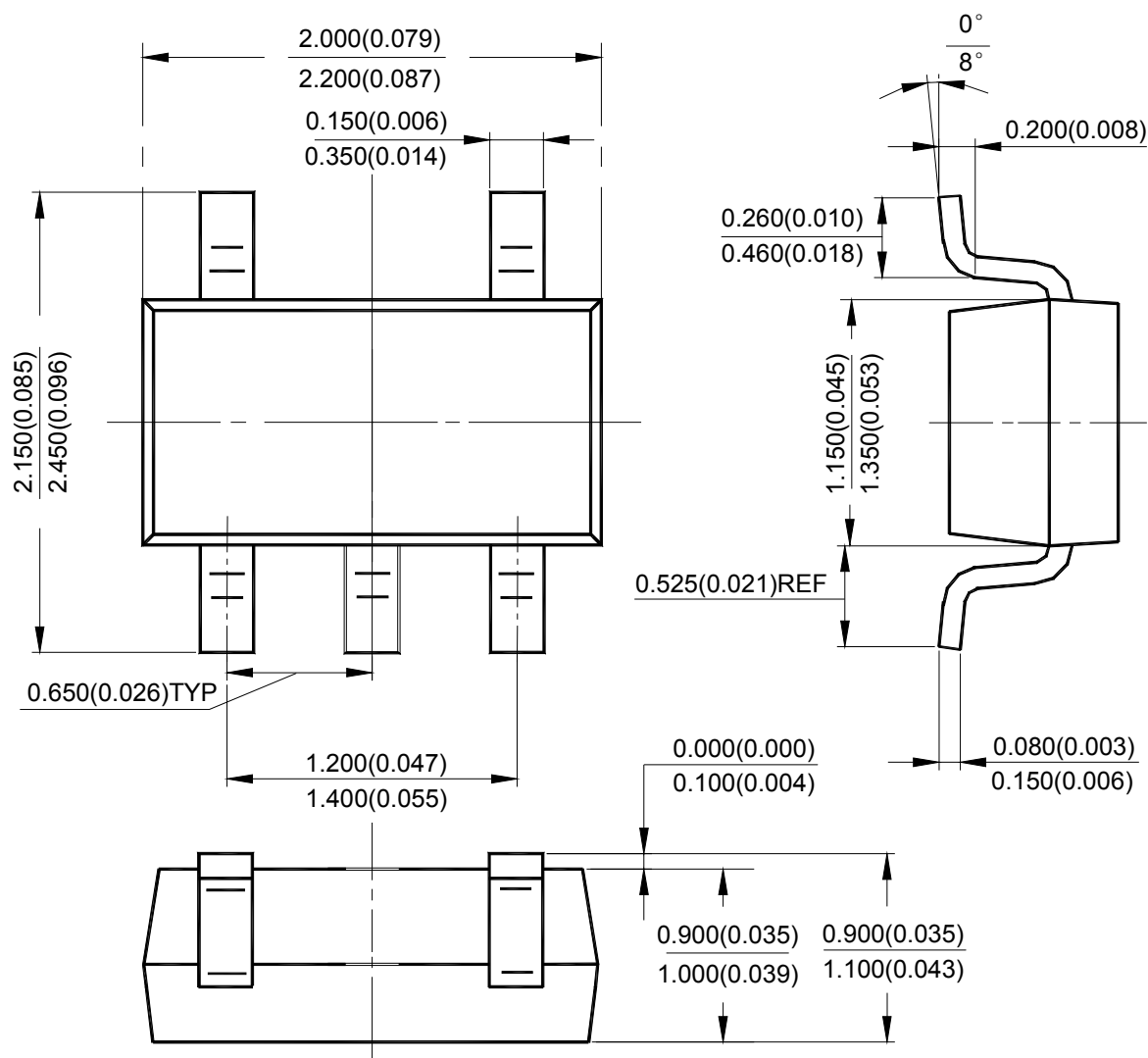
Figure 21. THD+N vs. Frequency



Mechanical Dimensions

SC-70-5

Unit: mm(inch)

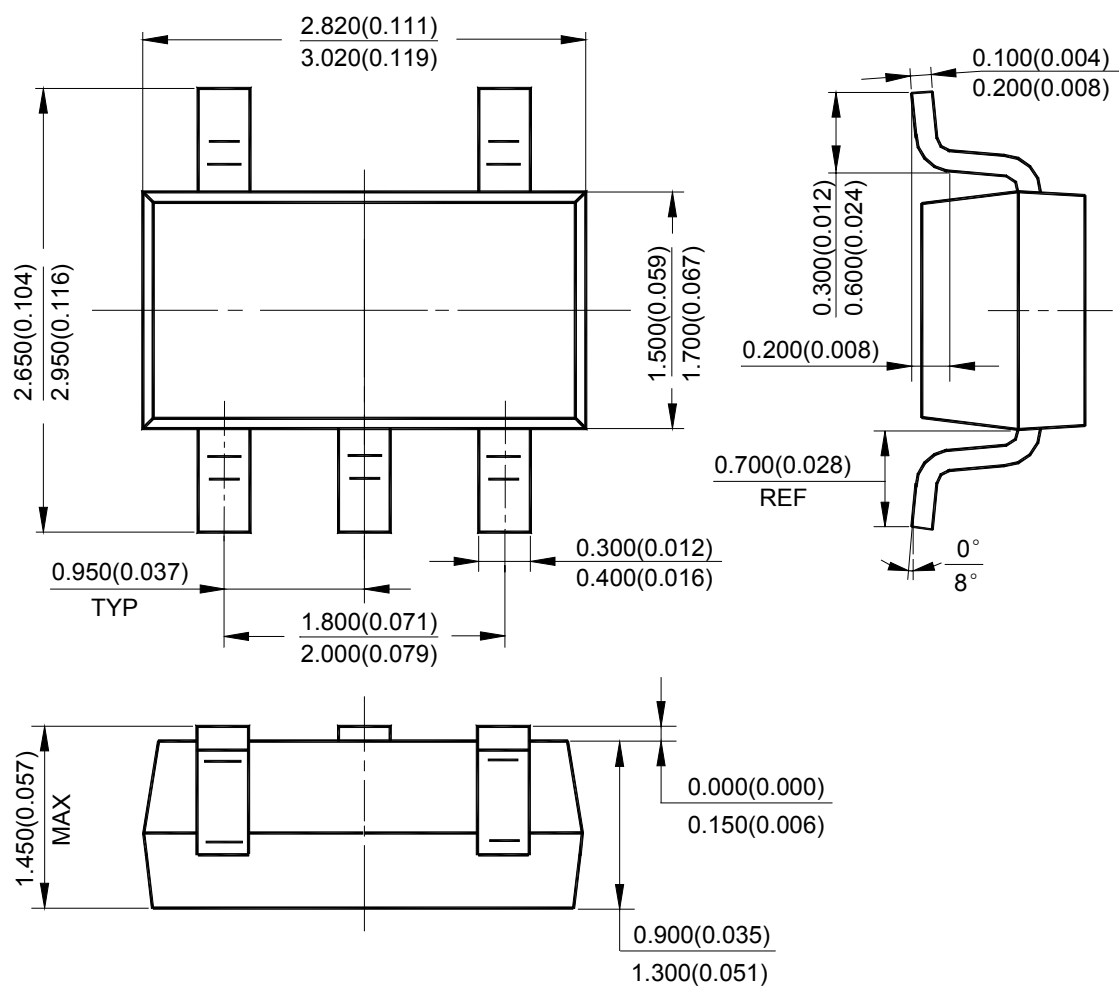




Mechanical Dimensions

SOT-23-5

Unit: mm(inch)





BCD Semiconductor Manufacturing Limited

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MAIN SITE

- Headquarters

BCD Semiconductor Manufacturing Limited

No. 1600, Zi Xing Road, Shanghai ZiZhu Science-based Industrial Park, 200241, China
Tel: +86-21-24162266, Fax: +86-21-24162277

- Wafer Fab

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd.

800 Yi Shan Road, Shanghai 200233, China
Tel: +86-21-6485 1491, Fax: +86-21-5450 0008

REGIONAL SALES OFFICE

Shenzhen Office

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd., Shenzhen Office

Unit A Room 1203, Skyworth Bldg., Gaoxin Ave. I.S., Nanshan District, Shenzhen, China
Tel: +86-755-8826 7951
Fax: +86-755-8826 7865

Taiwan Office

BCD Semiconductor (Taiwan) Company Limited

4F, 298-1, Rui Guang Road, Nei-Hu District, Taipei, Taiwan
Tel: +886-2-2656 2808
Fax: +886-2-2656 2806

USA Office

BCD Semiconductor Corp.

30920 Huntwood Ave. Hayward, CA 94544, USA
Tel : +1-510-324-2988
Fax: +1-510-324-2788